

FCX1051A SOT89 NPN medium power transistor

Summary

BV_{CEO} > 40V I_{C(cont)} = 3A V_{CE(sat)} < 120mV @ 1A R_{CE(sat)} = 57mΩ

 $P_D = 2W$

Complimentary type - FCX1151A

Description

An NPN low voltage, high gain bipolar transistor offering very low saturation voltage and excellent current handling in the SOT89 package.

Features

- Very low saturation voltage
- High gain
- Small outline package

Applications

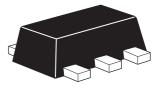
- Motor drive
- Strobe flash
- MOSFET and IGBT gate driving
- DC -DC converters

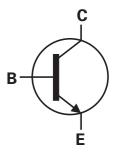
Ordering information

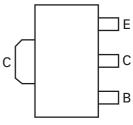
Device	Reel size	Tape width	Quantity
	(inches)	(mm)	per reel
FCX1051ATA	7	12	1,000

Device mark

051







Pinout - top view

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Collector-base voltage	V _{CBO}	150	V
Collector-emitter voltage	V _{CEO}	40	V
Emitter-base voltage	V _{EBO}	5	V
Peak pulse current ^(a)	I _{CM}	10	A
Continuous collector current	I _C	3	A
Power dissipation at T _{amb} = 25°C	P _{tot}	1 ^(b)	W
		2 ^(c)	W
Operating and storage temperature range	T _j ;T _{stg}	-55 to +150	°C

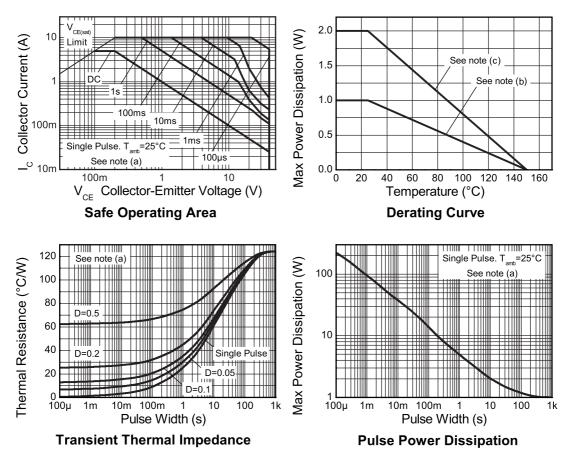
NOTES:

(a) Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤2%. Spice parameter data is available upon request for these devices. Refer to the handling instructions for soldering surface mount components.

(b) Recommended P_{tot} calculated using FR4 measuring 15x15x0.6mm.

(c) Maximum power dissipation is calculated assuming that the device is mounted on FR4 substrate measuring 40x40x0.6mm and using comparable measurement methods adopted by other suppliers.

Typical characteristics



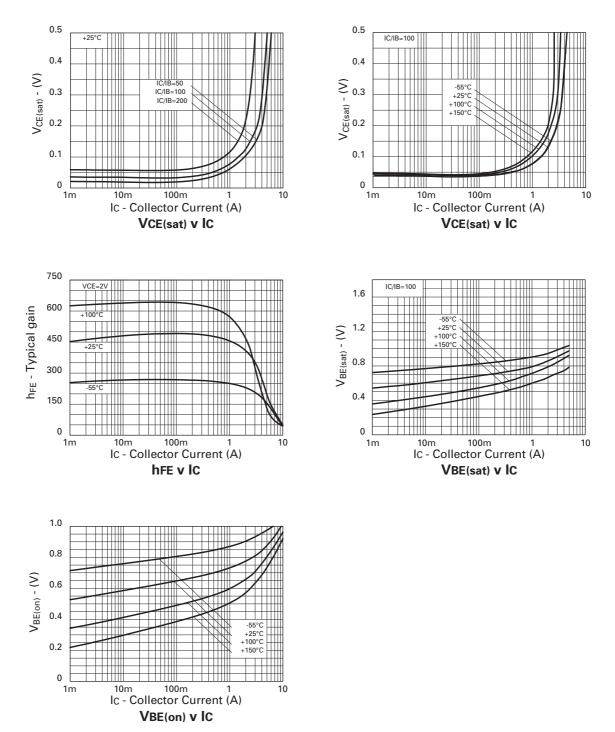
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	V _{(BR)CBO}	150			V	I _C = 100μA
Collector-emitter breakdown voltage	V _{CES}	150			V	I _C = 100μA
Collector-emitter breakdown voltage	V _{CEO}	40			V	I _C = 10mA
Collector-emitter breakdown voltage	V _{CEV}	150			V	I _C =100μA, V _{EB} = 1V
Emitter-base breakdown voltage	V _{(BR)EBO}	5			V	I _E = 100μA
Collector cut-off current	I _{CBO}		0.3	10	nA	V _{CB} = 120V
Emitter cut-off current	I _{EBO}		0.3	10	nA	$V_{EB} = 4V$
Collector emitter cut- off current	I _{CES}		0.3	10	nA	V _{CES} = 120V
Collector-emitter	V _{CE(sat)}		17	25	mV	I _C = 0.2A, I _B = 10mA ^(*)
saturation voltage			85	120	mV	I _C = 1A, I _B = 10mA ^(*)
			140	180	mV	I _C = 2A, I _B = 20mA ^(*)
			170	250	mV	I _C = 3A, I _B = 40mA ^(*)
			250	340	mV	I _C = 5A, I _B = 100mA ^(*)
Base-emitter saturation voltage	V _{BE(sat)}		880	1000	mV	I _C = 3A, I _B = 40mA ^(*)
Base-emitter turn-on voltage	V _{BE(on)}		840	950	mV	$I_{C} = 3A, V_{CE} = 2V^{(*)}$
Static forward current	h _{FE}	290	440	1200		I_{C} = 10mA, V_{CE} = 2V ^(*)
transfer ratio		270	450			$I_{C} = 1A, V_{CE} = 2V^{(*)}$
		270	360			$I_{C} = 3A, V_{CE} = 2V$ (*)
		130	220			$I_{C} = 5A, V_{CE} = 2V^{(*)}$
		40	55			$I_{C} = 5A, V_{CE} = 2V^{(*)}$ $I_{C} = 10A, V_{CE} = 2V^{(*)}$
Transition frequency	f _T		155		MHz	I _C = 50mA, V _{CE} = 10V f = 100MHz
Output capacitance	C _{obo}		27	40	pF	V _{CB} = 10V, f = 1MHz
Switching times	t _{on}		220		ns	$I_{C} = 3A, I_{B} = 30mA, V_{CC} = 10V$
	t _{off}		540		ns	$I_{C} = 3A, I_{B} = 30mA, V_{CC} = 10V$

Electrical characteristics (@ $T_{amb} = 25^{\circ}C$ unless otherwise stated)

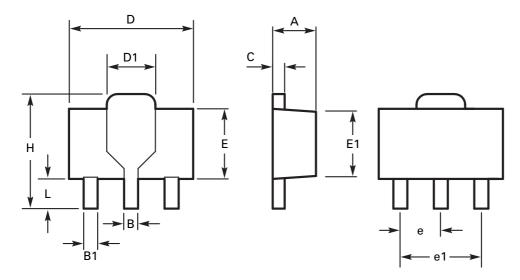
NOTES:

(*) Measured under pulsed conditions. Pulse width=300 $\mu s.$ Duty cycle ${\leq}2\%.$

Typical characteristics



Package outline - SOT89



DIM	Millin	neters	Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
В	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	е	1.50 BSC		0.059 BSC	
С	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	Н	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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